

描述 / Descriptions

SOT-23 塑封封装 NPN 半导体三极管。Silicon NPN transistor in a SOT-23 Plastic Package.

特征 / Features

饱和压降低，与 FMMT591 互补，无卤产品。

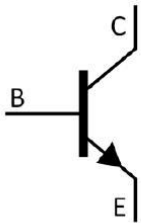
low equivalent On-resistance, Complementary pair with FMMT591, HF Product.

用途 / Applications

用于中功率放大。

Medium power amplifier applications.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : Base

PIN 2 : Emitter

PIN 3 : Collector

印章代码 / Marking

h_{FE} Range	100~300
Marking	H491

极限参数 / Absolute Maximum Ratings(Ta=25°C)

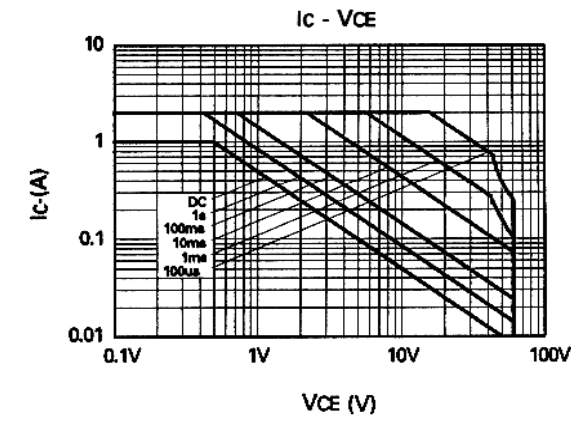
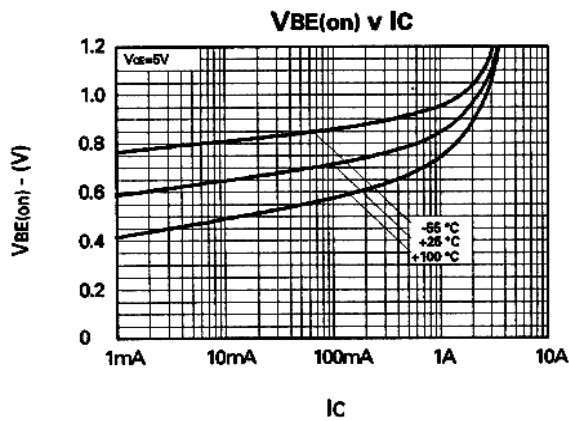
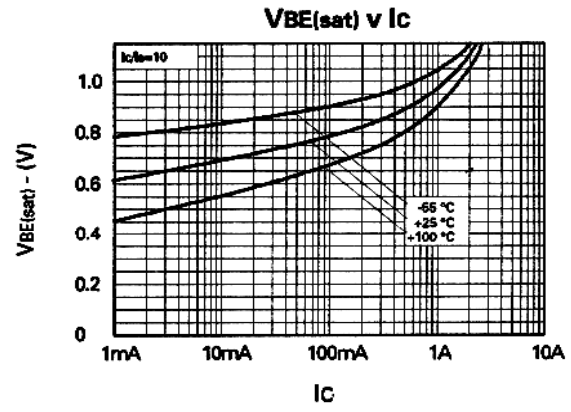
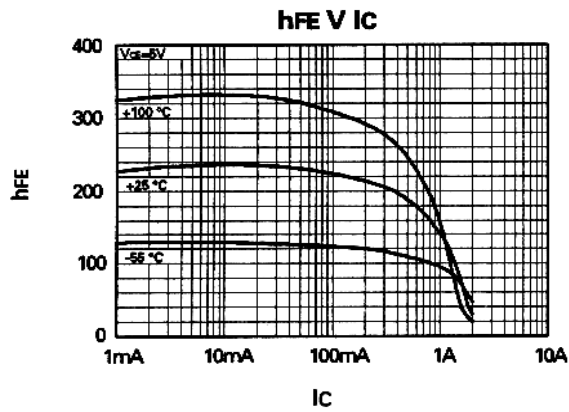
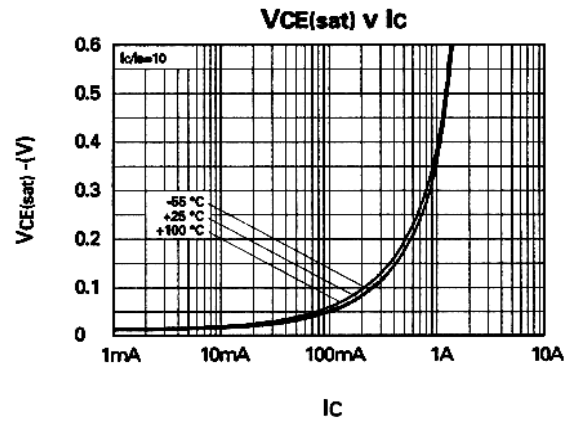
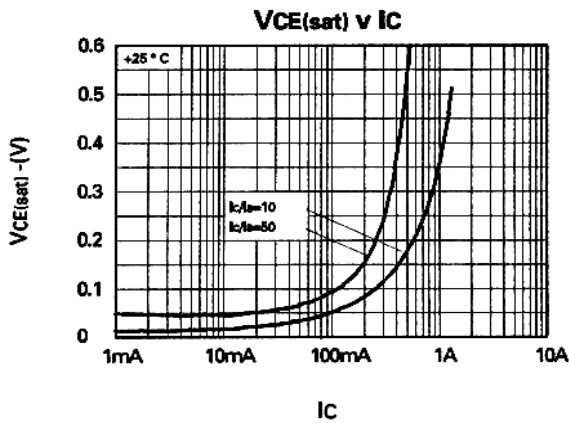
参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	80	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	1.0	A
Peak Pluse Current	I_{CM}	2.0	A
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=100\mu A$ $I_E=0$	80			V
Collector to Emitter Breakdown Voltage	$*V_{CEO}$	$I_C=10mA$ $I_B=0$	60			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=100\mu A$ $I_C=0$	5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=60V$ $I_E=0$			0.1	μA
Collector Cut-Off Current	I_{CES}	$V_{CES}=60V$ $I_E=0$			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=4.0V$ $I_E=0$			0.1	μA
DC Current Gain	$*h_{FE(1)}$	$V_{CE}=5.0V$ $I_C=500mA$	100		300	
	$*h_{FE(2)}$	$V_{CE}=5.0V$ $I_C=1.0mA$	100			
	$*h_{FE(3)}$	$V_{CE}=5.0V$ $I_C=1.0A$	80			
	$*h_{FE(4)}$	$V_{CE}=5.0V$ $I_C=2.0A$	30			
Collector to Emitter Saturation Voltage	$*V_{CE(sat)(1)}$	$I_C=500mA$ $I_B=50mA$			0.25	V
	$*V_{CE(sat)(2)}$	$I_C=1.0A$ $I_B=100mA$			0.5	V
Base to Emitter Saturation Voltage	$*V_{BE(sat)}$	$I_C=1.0A$ $I_B=100mA$			1.1	V
Base-Emitter On Voltage	$*V_{BE(on)}$	$V_{CE}=5.0V$ $I_C=1.0A$			1.0	V
Transition Frequency	f_T	$V_{CE}=10V$ $f=100MHz$ $I_C=50mA$	150			MHz
Collector-Base Breakdown Voltage	C_{obo}	$V_{CB}=10V$ $f=1.0MHz$			10	pF

*Pulsed test: pulse width=300 μs . Duty cycle $\leq 2\%$

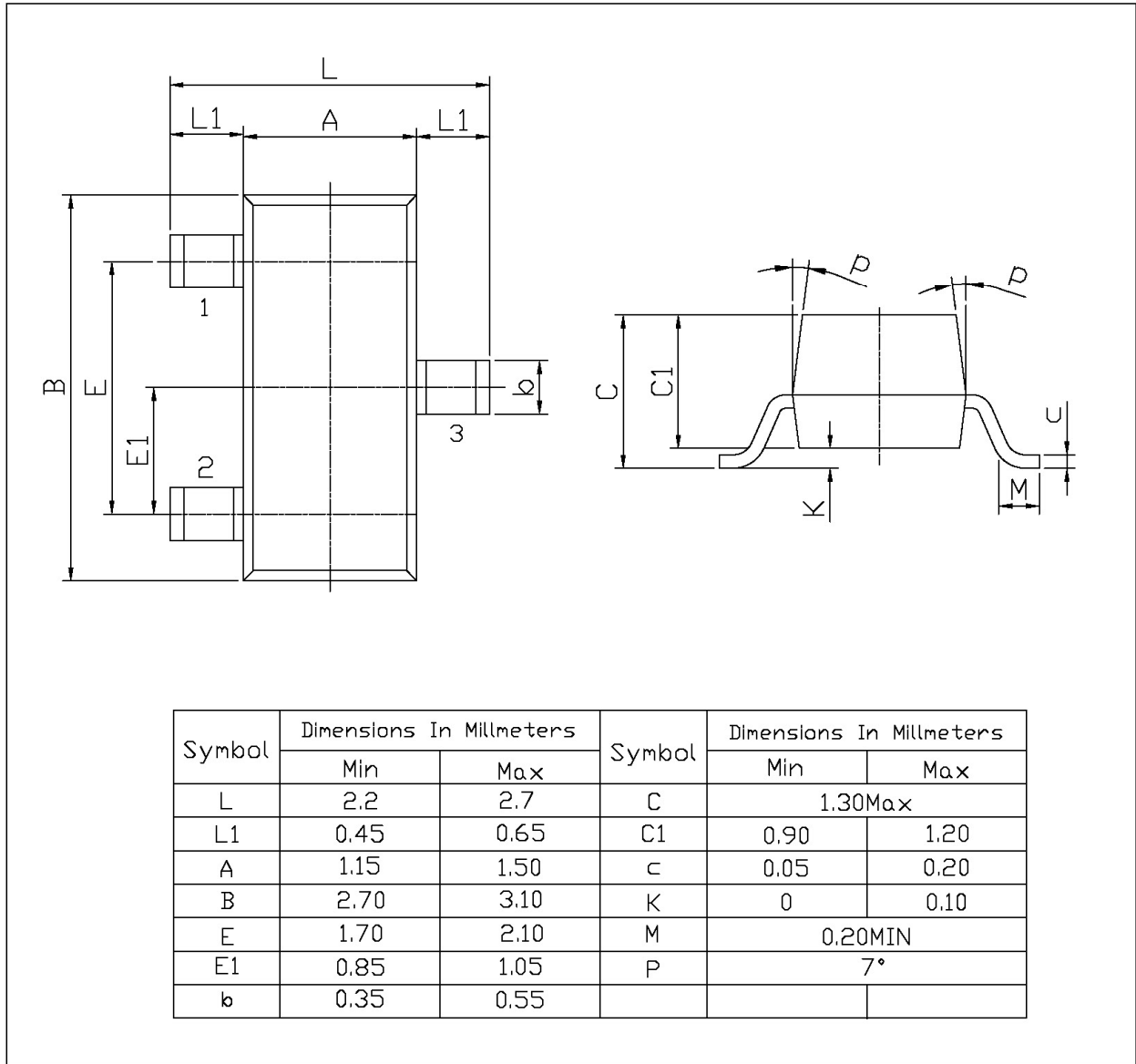
电参数曲线图 / Electrical Characteristic Curve



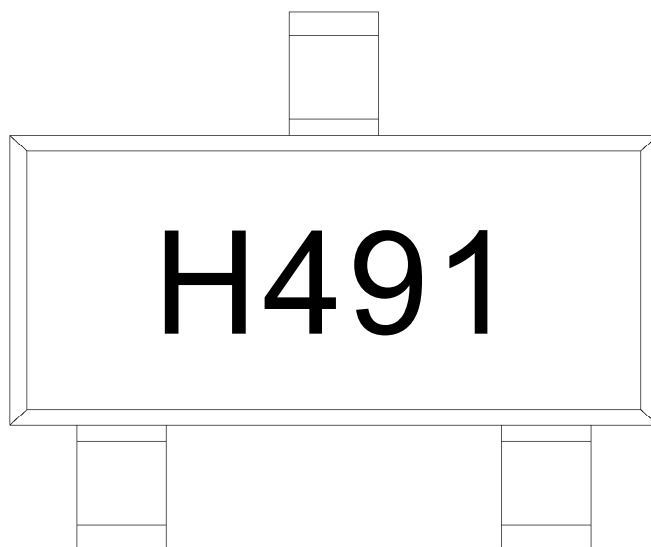
外形尺寸图 / Package Dimensions

SOT-23

单位: mm



印章说明 / Marking Instructions



说明：

H： 为公司代码

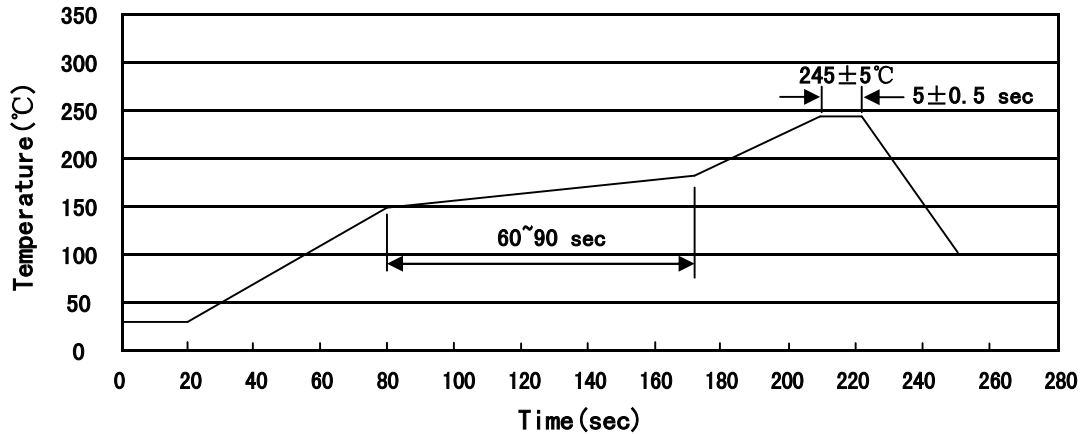
491： 为型号代码

Note:

H: Company Code.

491: Product Type Code.

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-23	3,000	10	30,000	6	180,000	7" ×8	180×120×180	390×385×205

使用说明 / Notices